

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	2	6486067.pn.	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2004/02/19 16:48	
2	BRS	L2	14775	(cvd or chemical near vapor near deposition) near3 (oxide)	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2004/02/19 16:48	
3	BRS	L3	3378	(cvd or chemical near vapor near deposition) near3 (oxide) near15 (wafer or substrate)	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2004/02/19 16:49	
4	BRS	L4	1	(cvd or chemical near vapor near deposition) near3 (oxide) near15 (wafer or substrate) near25 (poly\$5 and silicide)	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2004/02/19 16:50	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	106	(cvd or chemical near vapor near deposition) near3 (oxide) near15 (wafer or substrate) near25 (poly\$5 or silicide)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB-	2004/02/19 17:02	
6	BRS	L6	52	(cvd or chemical near vapor near deposition) near (oxide) near15 (wafer or substrate) near25 (poly\$5 or silicide)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB-	2004/02/19 17:05	
7	BRS	L7	440	(cvd or chemical near vapor near deposition) near25 (oxide) near15 (wafer or substrate) near25 (poly\$5 or silicide)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB-	2004/02/19 17:05	
8	BRS	L8	14	(cvd or chemical near vapor near deposition) near25 (oxide) near15 (wafer or substrate) near25 (poly\$5 and silicide)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM_TDB-	2004/02/19 17:06	